Octal Bus Buffer

The MC74VHC244 is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology.

The MC74VHC244 is a noninverting 3-state buffer, and has two active-low output enables. This device is designed to be used with 3-state memory address drivers, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed: $t_{PD} = 3.9 \text{ ns}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A \text{ (Max)}$ at $T_A = 25^{\circ}\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 0.9 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V Machine Model > 200 V
- Chip Complexity: 136 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

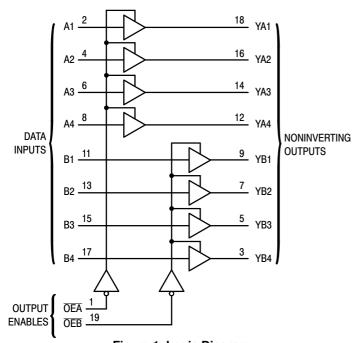


Figure 1. Logic Diagram



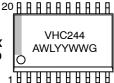
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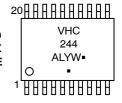
MARKING DIAGRAMS



SOIC-20 DW SUFFIX CASE 751D







VHC244 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information in the Ordering Information Table on page 2 of this data sheet.

FUNCTION TABLE

INP	OUTPUTS	
OEA, OEB	A, B	YA, YB
L	L	L
L	Н	Н
Н	Х	Z

ORDERING INFORMATION

Device	Package	Shipping [†]	
MC74VHC244DWR2G	SOIC-20 WB (Pb-Free)	1000/Tape & Reel	
MC74VHC244DTG		75 Units/Rail	
MC74VHC244DTR2G	TSSOP-20 (Pb-Free)	2500/Tape & Reel	
NLV74VHC244DTR2G*	(/	2500/Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS (Note 1)

Symbol	Р	arameter	Value	Unit
V _{CC}	Positive DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	Digital Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage		-0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current		-20	mA
lok	Output Diode Current		±20	mA
l _{out}	DC Output Current, per Pin		±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	3	±75	mA
P _D	Power Dissipation in Still Air	SOIC TSSOP	500 450	mW
T _{STG}	Storage Temperature Range		-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 >2000	V
I _{LATCHUP}	Latchup Performance	Above $\rm V_{CC}$ and Below GND at 125°C (Note 5)	±300	mA
$\theta_{\sf JA}$	Thermal Resistance, Junction-to-Amb	ient SOIC TSSOP	96 128	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{in} and V_{out} should be constrained to the range GND $\leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage

- Tested to EIA/JESD22-A114-A
 Tested to EIA/JESD22-A115-A
- 4. Tested to JESD22-C101-A
- 5. Tested to EIA/JESD78

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V _{CC}	DC Supply Voltage		2.0	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage		0	V _{CC}	V
T _A	Operating Temperature Range, all Package Types		-55	125	°C
t _r , t _f	Input Rise or Fall Time	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

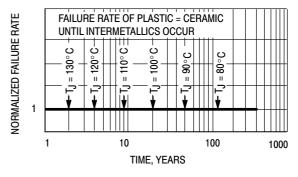


Figure 2. Failure Rate vs. Time Junction Temperature

DC CHARACTERISTICS (Voltages Referenced to GND)

			V _{CC}	1	Γ _A = 25°0	С	T _A ≤	85°C	-55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level		2.0	1.5			1.5	1.5	1.5		V
	Input Voltage		3.0 to 5.5	V _{CCX} 0.7			V _{CCX} 0.7	V _{CCX} 0.7	V _{CCX} 0.7		
V_{IL}	Maximum Low-Level		2.0			0.5		0.5		0.5	V
	Input Voltage		3.0 to 5.5			V _{CCX} 0.3		V _{CCX} 0.3		V _{CCX} 0.3	
V_{OH}	Maximum High-Level	$V_{IN} = V_{IH}$ or V_{IL}	2.0	1.9	2.0		1.9		1.9		V
	Output Voltage	I _{OH} = -50 μA	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$	3.0	2.58			2.48		2.34		
		I _{OH} = -8 mA	4.5	3.94			3.8		3.66		
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = 4$ mA $I_{OH} = 8$ mA	3.0		0.0	0.36		0.44		0.52 0.52	-
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I _{OZ}	Maximum 3–State Leakage Current	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	5.5			±0.25		±2.5		±2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current (per package)	V _{IN} = V _{CC} or GND	5.5			4.0		40.0		40.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

				T _A = 2	25°C	T _A ≤	85°C		C ≤ T _A 25°C	
Symbol	Parameter	Test Conditions	М	in Typ	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to YA or	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 3.3 \pm 0.3 \text{ V}$ $C_L = 3.3 \pm 0.3 \text{ V}$	15 pF 50 pF	5.8 8.3		1.0 1.0	10.0 13.5	1.0 1.0	11.0 14.5	ns
	B to YB	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 6$ $C_L = 6$		3.9 5.4		1.0 1.0	6.5 8.5	1.0 1.0	7.5 9.5	
t _{PZL} , t _{PZH}	Output Enable Time OEA to YA or	$\begin{aligned} &V_{CC}=3.3\pm0.3 \ V & C_L=3.3 \\ &R_L=1 \ k\Omega & C_L=3.3 \end{aligned}$		6.6 9.1		1.0 1.0	12.5 16.0	1.0 1.0	13.5 17.0	ns
(OEB to YB	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 6.0 \pm 0.1 \text{ C}$ $C_L = 6.0 \pm 0.1 \text{ C}$		4.7 6.2		1.0 1.0	8.5 10.5	1.0 1.0	9.5 11.5	
t _{PLZ} , t _{PHZ}	Output Disable Time OEA to YA or	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 8$ $R_L = 1 \text{ k}\Omega$	50 pF	10.	3 14.0	1.0	16.0	1.0	17.0	ns
	OEB to YB	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 8$ $R_L = 1 \text{ k}\Omega$	50 pF	6.7	9.2	1.0	10.5	1.0	11.5	
t _{OSLH} , t _{OSHL}	Output to Output Skew	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 9.00 \text{ (Note 6)}$	50 pF		1.5		1.5		1.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 9$ (Note 6)	50 pF		1.0		1.0		1.5	
C _{in}	Maximum Input Capacitance			4	10		10		10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)			6						pF

		Typical @ 25°C, V _{CC} = 5.0V		
C_{PD}	Power Dissipation Capacitance (Note 7)	19	pF	

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$, $C_L = 50 \text{ pF}$, $V_{CC} = 5.0 \text{ V}$)

		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.6	0.9	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.6	-0.9	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

 ^{6.} Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 7. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC} • f_{in} + I_{CC} • V_{CC}.

SWITCHING WAVEFORMS

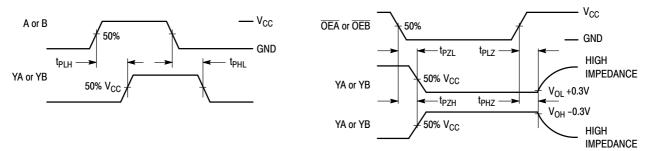
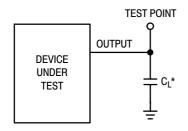


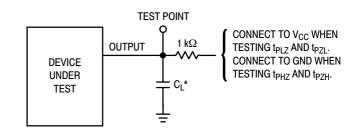
Figure 3. Switching Waveform

Figure 4. Switching Waveform

TEST CIRCUITS



*Includes all probe and jig capacitance



*Includes all probe and jig capacitance

Figure 5. Test Circuit

Figure 6. Test Circuit

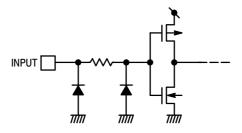
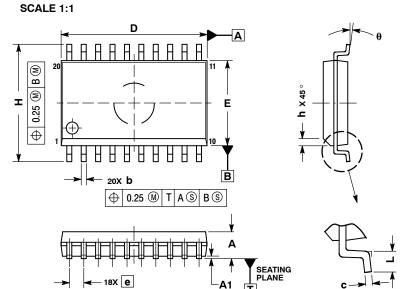


Figure 7. Input Equivalent Circuit



SOIC-20 WB CASE 751D-05 **ISSUE H**

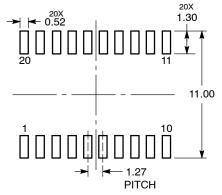
DATE 22 APR 2015



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

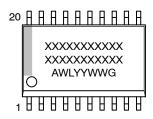
	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
b	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	E 7.40			
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
A	0 °	7 °		

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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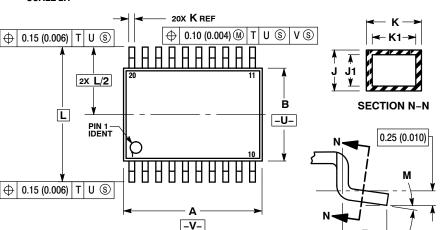
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

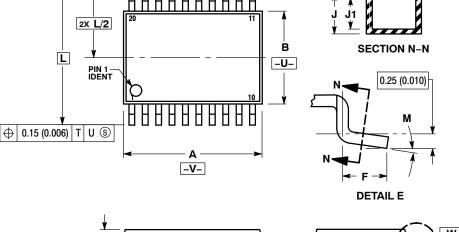
0.100 (0.004) -T- SEATING

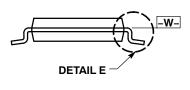


TSSOP-20 WB CASE 948E ISSUE D

DATE 17 FEB 2016







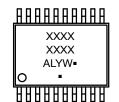
NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252		
М	0°	8°	0°	8°	

GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

SOLDERING FOOTPRINT		
7.	06 ───	
1		
₁	———— PITCH	
16X		
1.26	DIMENSIONS: MILLIMETERS	

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16X

0.36

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